

Supporting Information

Improved performance in TIPS-pentacene field effect transistors using solvent additives

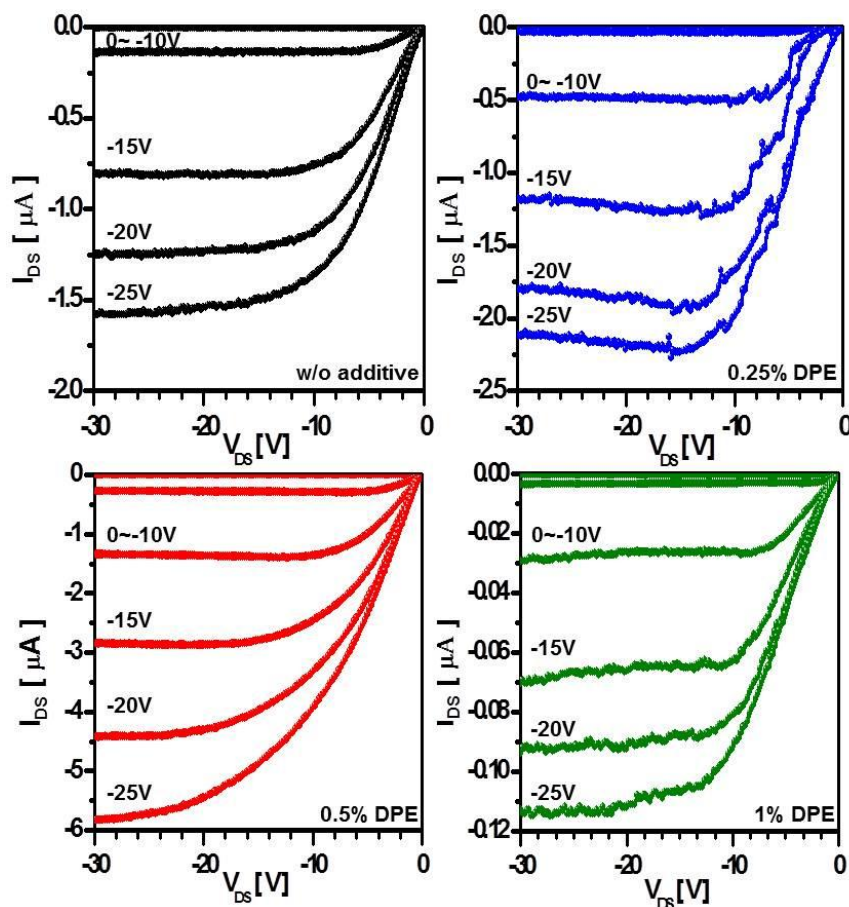
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Figure S1. Output characteristics of TIPS-pentacene FETs processed using various DPE concentrations.

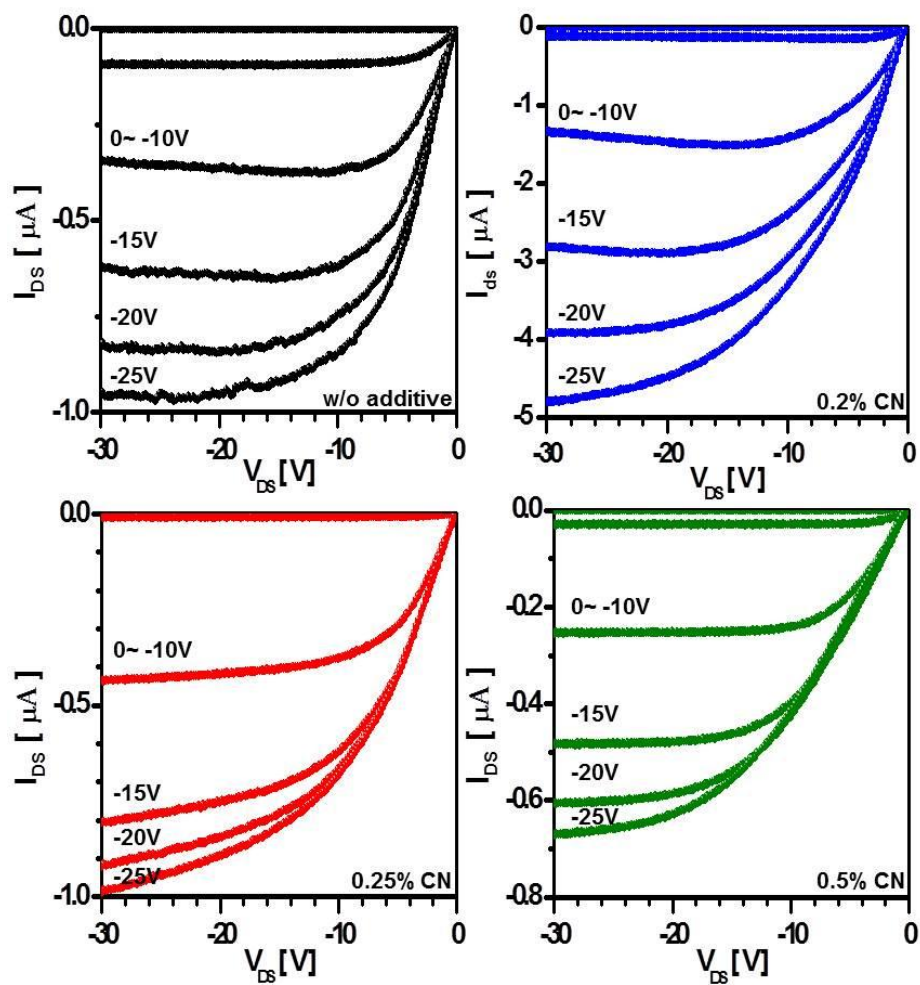


Figure S2. Output characteristics of TIPS-pentacene FETs processed using various CN concentrations.

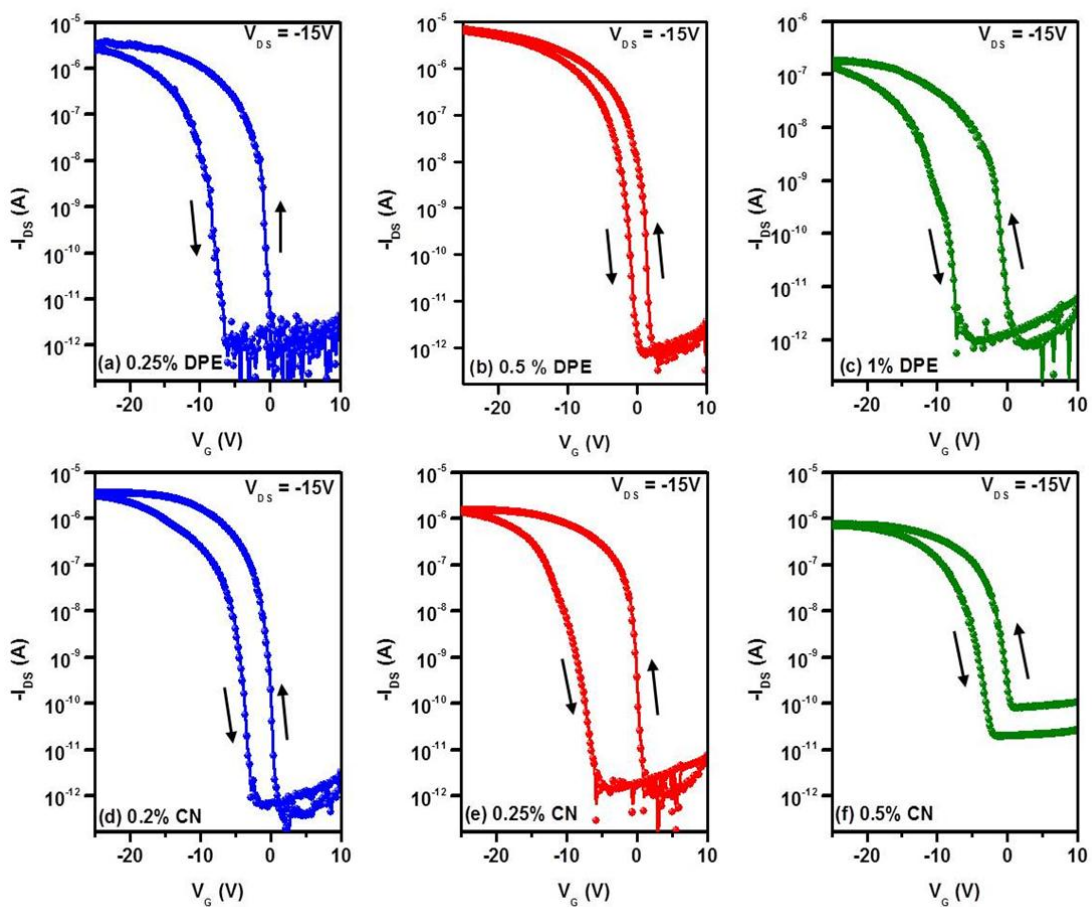


Figure S3. Transfer hysteresis characteristics of TIPS-pentacene FETs with various concentration of DPE and CN.

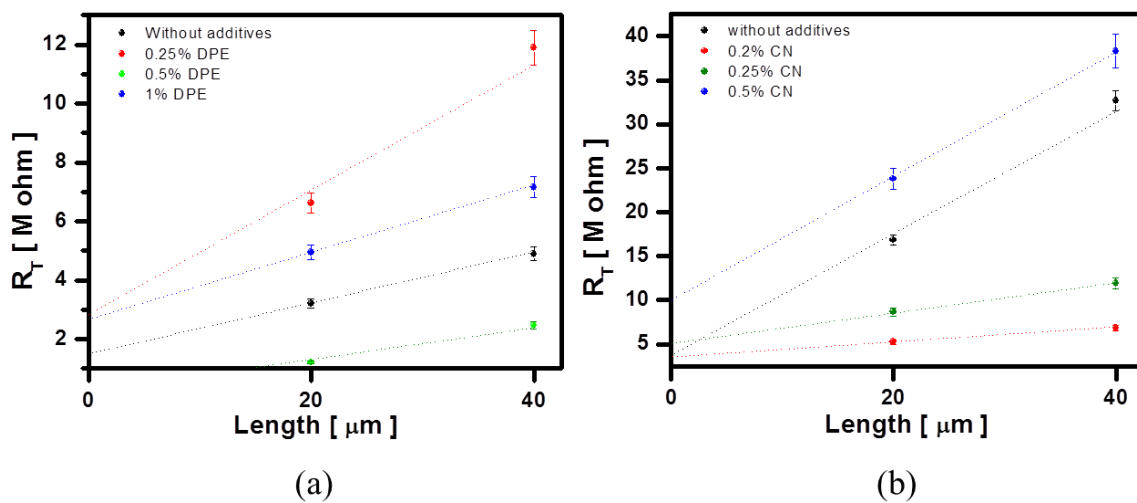


Figure S4. Total resistance (R_T) vs. channel length of TIPS-pentacene FETs with (a) DPE and (b) CN at different additive concentrations.

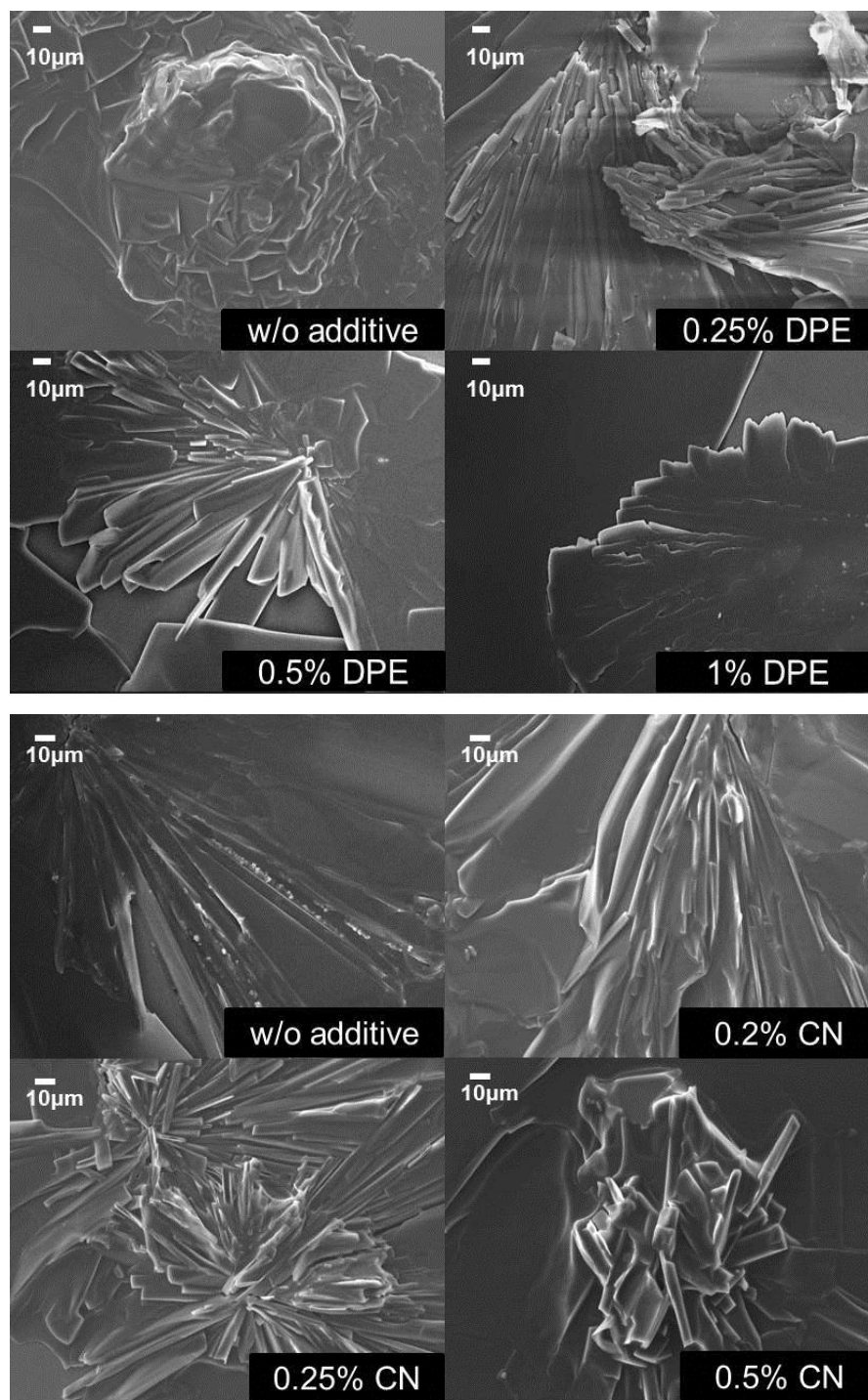


Figure S5. SEM images ($\times 500$) of TIPS-pentacene films processed with various DPE (top) and CN (bottom) concentrations.

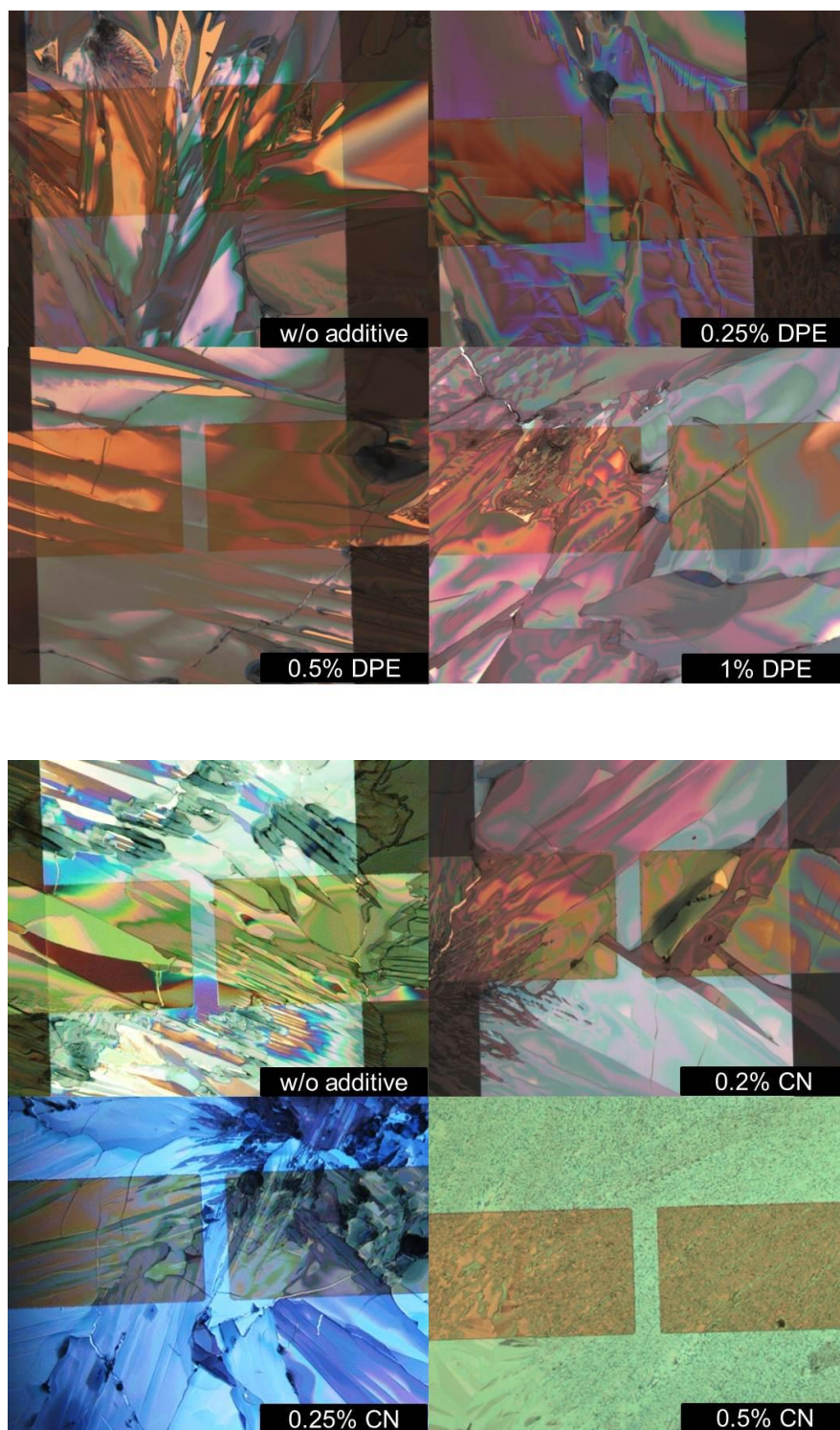


Figure S6. Optical microscope images of TIPS-pentacene FETs processed with various DPE (top) and CN (bottom) concentrations.

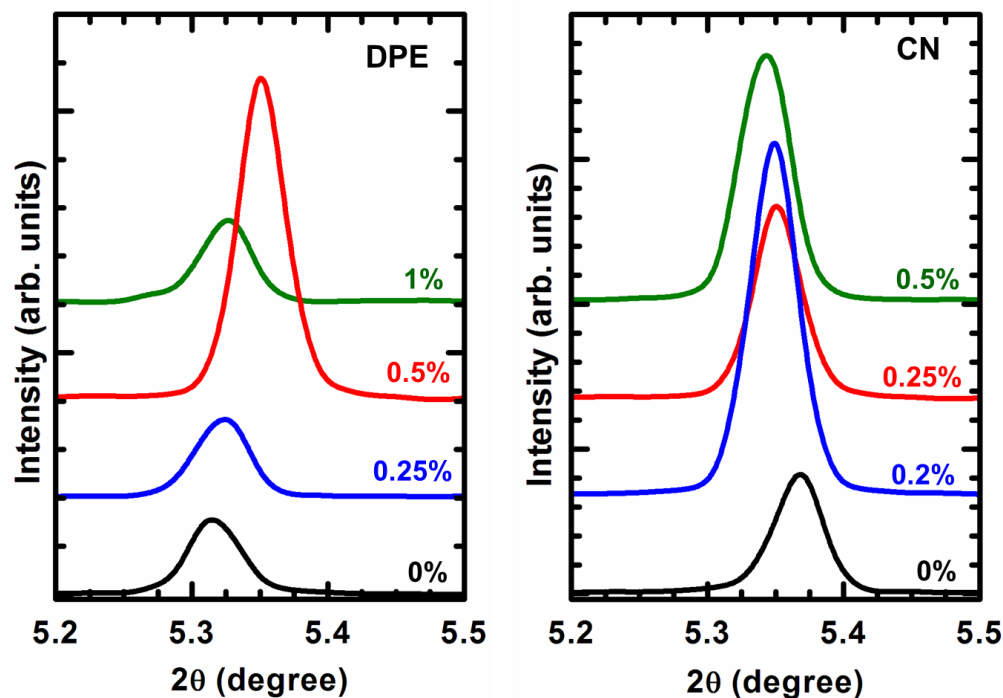


Figure S7. XRD (001) peaks for TIPS-pentacene films processed with various concentrations of DPE (left) and CN (right).

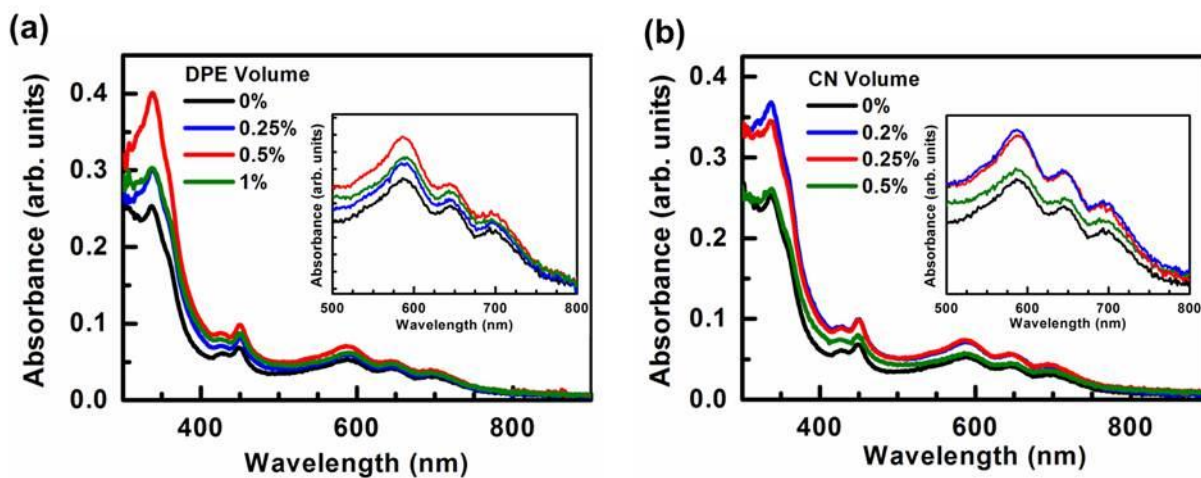


Figure S8. UV-Vis absorption spectra of TIPS-pentacene films processed with (a) DPE and (b) CN prepared using different additive concentrations.